

Product Summary

The GESDBU5V0Y1M is designed to protect voltage sensitive electronic components from ESD and other transients. Excellent clamping capability, low leakage, low capacitance, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in digital cameras, cellular phones and many other portable applications where board space is at a premium.

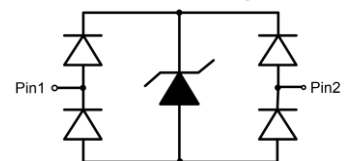
Feature

- Low Reverse Stand-Off Voltage: 5.0V
- IEC61000-4-4(EFT):40A(5/50ns)
- IEC61000-4-5(Surge):5.5A (8/20us)
- Very Low Reverse Current: $I_R < 0.2\mu A$ (typical)
- Line Capacitance: 0.30pF (typical) @ 1MHz
- Bi-Directional

Application

- Cellular phones
- Portable devices
- Digital cameras
- Player
- Smart home
- Robot

Marking: 5U

DFN1006-2L**Schematic diagram**

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 ESD Voltage	$V_{\text{ESD}}^{(1)}$	± 30	KV
IEC 61000-4-2 ESD Voltage		± 30	
Peak Pulse Power	$P_{\text{PP}}^{(2)}$	60	W
Peak Pulse Current	$I_{\text{PP}}^{(2)}$	5.5	A
Junction Temperature	T_J	$-40 \sim +125$	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	$-55 \sim +155$	$^{\circ}\text{C}$

Notes:

- 1) Device stressed with ten non-repetitive ESD pulses.
- 2) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5.

ESD standards compliance

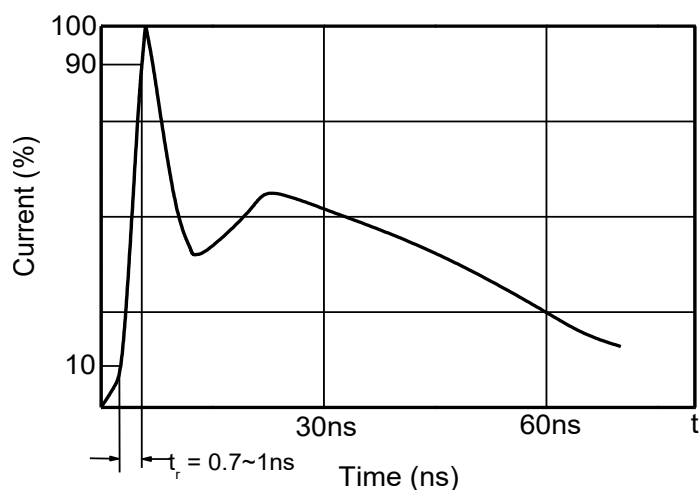
IEC61000-4-2 Standard

Contact Discharge		Air Discharge	
Level	Test Voltage kV	Level	Test Voltage kV
1	2	1	2
2	4	2	4
3	6	3	8
4	8	4	15

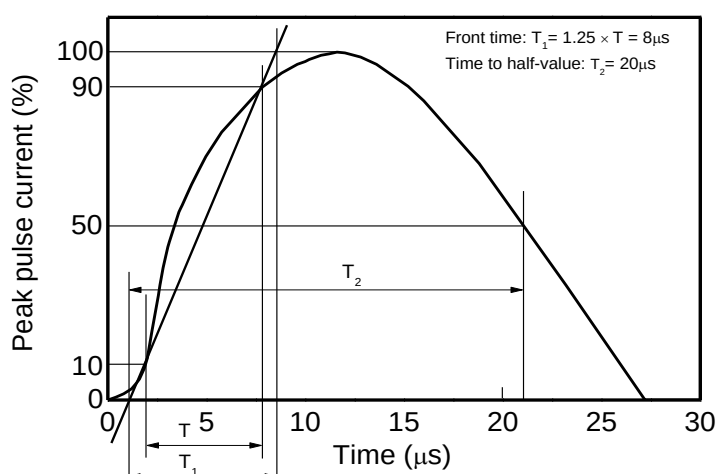
JESD22-A114-B Standard

ESD Class	Human Body Discharge V
0	0~249
1A	250~499
1B	500~999
1C	1000~1999
2	2000~3999
3A	4000~7999
3B	8000~15999

Contact discharge current waveform per IEC61000-4-2

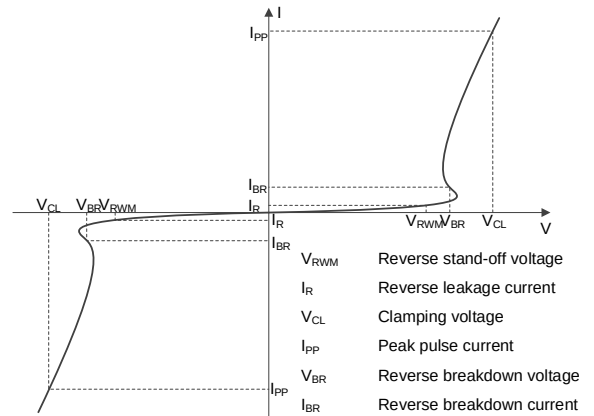


8/20 μs waveform per IEC61000-4-5



Electrical Parameter

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_{BR}
I_{BR}	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Standoff Voltage



V-I characteristics for a Bi-directional TVS

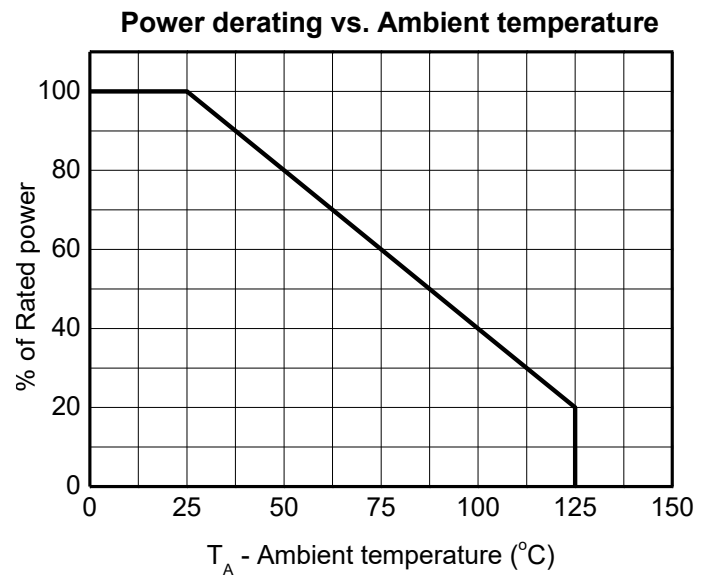
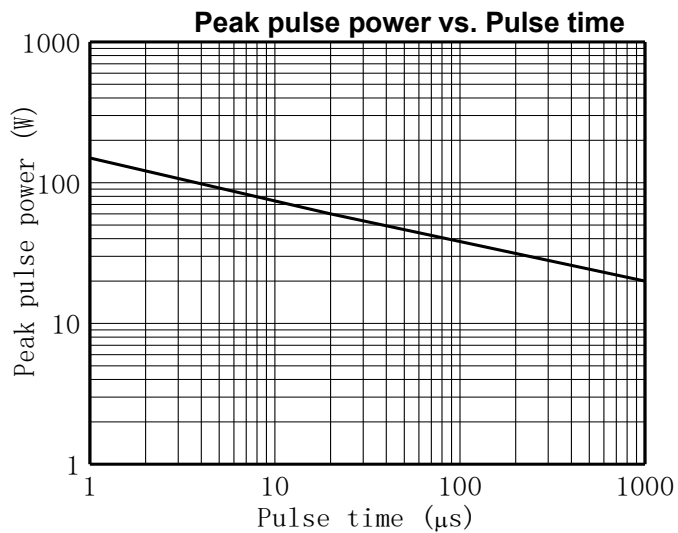
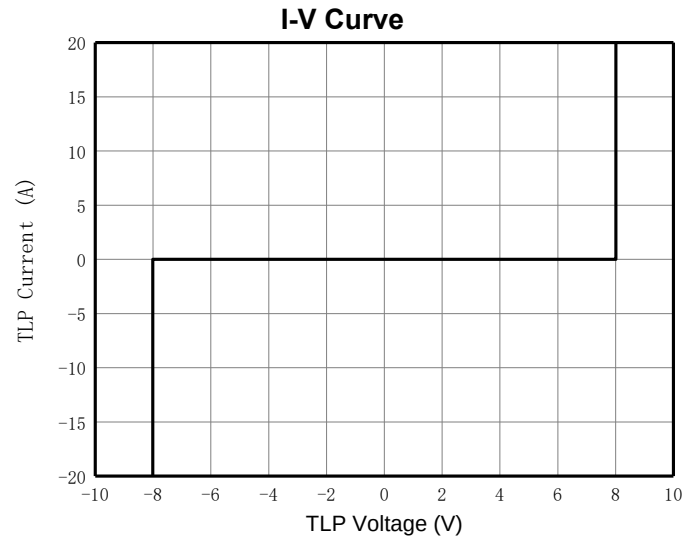
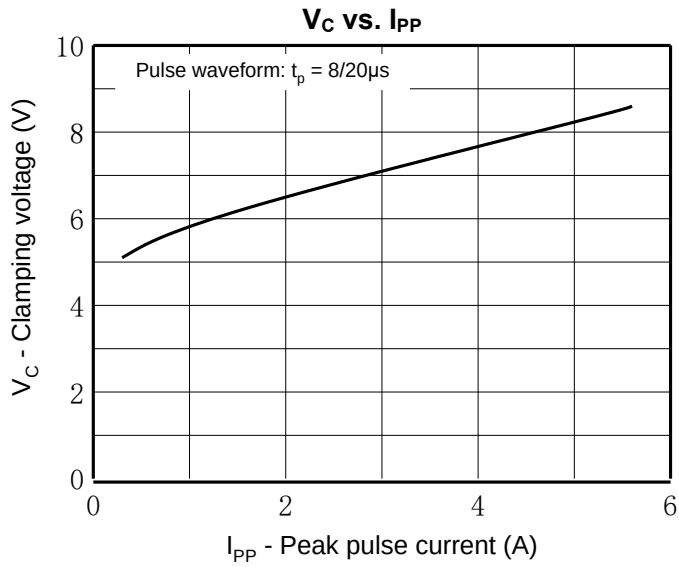
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse Standoff Voltage	$V_{RWM}^{1)}$				5.0	V
Reverse Leakage Current	I_R	$V_{RWM}=5.0\text{V}$			0.2	μA
Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	6.0	7.5	9.0	V
Clamping Voltage	$V_C^{2)}$	$I_{PP}=1\text{A}$		6	7.5	V
		$I_{PP}=5.5\text{A}$		8.5	11	V
Junction Capacitance	C_j	$V_R=0\text{V}, f=1\text{MHz}$		0.25	0.4	pF
		$V_R=0\text{V}, f=1\text{GHz}$		0.18		pF

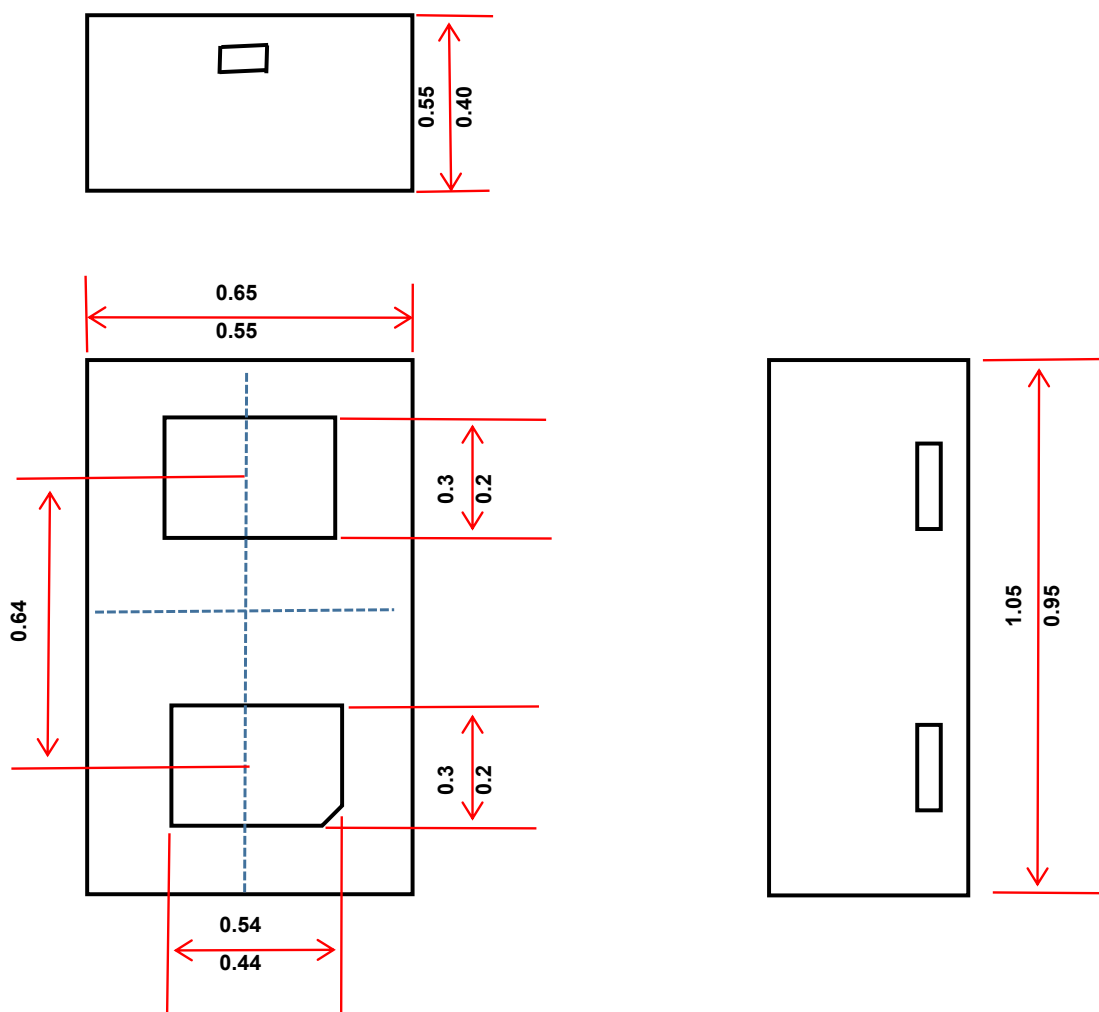
Notes:

- Other voltages available upon request.
- Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

Typical Characteristics



DFN1006-2L Package Outline Dimensions



Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.